MOS INTEGRATED CIRCUIT μ PD16833A

MONOLITHIC QUAD H BRIDGE DRIVER CIRCUIT

DESCRIPTION

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The μ PD16833A is a monolithic quad H bridge driver IC which uses power MOS FETs in its driver stage. By using the MOS FETs in the output stage, this driver IC has a substantially improved saturation voltage and power consumption as compared with conventional driver circuits using bipolar transistors.

A low-voltage malfunction prevention function is provided to prevent the IC from malfunctioning when the supply voltage drops. By eliminating the charge pump circuit, the current during power-OFF is drastically decreased.

As the package, a 30-pin plastic shrink SOP is employed to enable the creation of compact, slim application sets.

This driver IC can drive two stepping motors at the same time, and is ideal for driving stepping motors in the lens of a video camera.

FEATURES

- Four H bridge circuits employing power MOS FETs
- Low current consumption by eliminating charge pump
 V_M pin current when power-OFF: 10 μA MAX. V_{DD} pin current: 10 μA MAX.
- Input logic frequency: 100 kHz
- 3-V power supply Minimum operating supply voltage: 2.5 V
- Low-voltage malfunctioning prevention circuit
- 30-pin plastic shrink SOP (300 mil) (μPD16833AG3)

ORDERING INFORMATION

Part Number	Package
μPD16833AG3	30-pin plastic shrink SOP (300 mil)

ABSOLUTE MAXIMUM RATINGS (T_A = 25 $^{\circ}$ C)

Parameter	Symbol	Conditions	Rating	Unit
Supply voltage	Vdd		-0.5 to +6.0	V
	Vм		-0.5 to +6.0	V
Input voltage	Vin		-0.5 to V _{DD} + 0.5	V
H bridge drive currentNote 1	DR (DC)	DC	±300	mA
Instantaneous H bridge drive currentNote 1	DR (pulse)	$PW \le 10 \text{ ms}, \text{ Duty} \le 5 \%$	±700	mA
Power dissipation Note 2	Рт		1.19	W
Peak junction temperature	Тсн (мах)		150	°C
Storage temperature range	Tstg		-55 to +150	°C

Notes 1. Permissible current per phase, when mounted on a printed circuit board

2. When mounted on a glass epoxy board (10 cm \times 10 cm \times 1 mm)

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Recommended Operating Conditions

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply voltage	Vdd	2.5		5.5	V
	Vм	2.7		5.5	V
H bridge drive current	ldr	-200		200	mA
Logic input frequency ^{Note}	fın			100	kHz
Operating temperature range	TA	-10		85	°C
Peak junction temperature	Тсн (мах)			125	°C

Note Common to IN and EN pins

DC Characteristics (Unless otherwise specified, VDD = VM = 3.0 V, TA = 25 °C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
OFF V _M pin current	IM (OFF)	with all control pins at low level			10	μA
VDD pin current	ldd	with all control pins at low level			10	μΑ
High-level input current	Ін	Vin =Vdd			0.06	mA
Low-level input current	١L	V _{IN} = 0	-1.0			μA
Input pull-down resistor	RIND		50		200	kΩ
High-level input voltage	Vін	VDD = 2.5 V to 5.5 V	$V_{DD} imes 0.7$		Vdd + 0.3	V
Low-level input voltage	VIL	VDD = 2.5 V to 5.5 V	-0.3		$V_{DD} imes 0.3$	V
H bridge ON resistance ^{Note}	Ron	V _{DD} = V _M = 2.7 V to 5.5 V			3.0	Ω
Low-voltage malfunction prevention circuit operating voltage	VDDS1	V _M = 5.0 V −10 °C ≤ T _A ≤ +85 °C	0.8		2.5	V
	Vdds2	V _M = 3.0 V −10 °C ≤ T _A ≤+85 °C	0.65		2.5	V

Note Sum of top and bottom ON resistances (@IDR = 100 mA)

AC Characteristics (Unless otherwise specified, $V_{DD} = V_M = 3.0 \text{ V}, \text{ T}_A = 25 \text{ }^{\circ}\text{C}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
H bridge output circuit turn-ON	tолн	$R_M = 20 \Omega$, Figure 1		0.7	20	μs
time						
H bridge output circuit turn-OFF	toffh			0.2	0.5	μs
time						
Rise time	tr		0.1	0.4	1.0	μs
Fall time	tr			70	200	ns

FUNCTION TABLE

Channel 1

EN1	IN ₁	OUT1A	OUT1B
н	L	н	L
н	Н	L	н
L	L	Z	Z
L	Н	Z	Z

Channel 3

EN₃	INз	OUT3A	OUT3B
н	L	н	L
н	н	L	Н
L	L	Z	Z
L	н	Z	Z

Channel 2

EN ₂	IN2	OUT2A	OUT2B
Н	L	Н	L
н	Н	L	н
L	L	Z	Z
L	Н	Z	Z

Channel 4

EN4	IN4	OUT4A	OUT4B
н	L	Н	L
Н	Н	L	Н
L	L	Z	Z
L	Н	Z	Z

H: High level, L: Low level, Z: High impedance IN

PIN CONFIGURATION

NC	1	30	NC
NC	2	29	NC
Vdd	3	28	DGND
V _{M1}	4	27	NC
1A	5	26	1B
PGND	6	25	PGND
2A	7	24	2B
ЗA	8	23	Vм2, з
PGND	9	22	3B
4A	10	21	PGND
V _{M4}	11	20	4B
IN1	12	19	EN4
EN1	13	18	IN ₄
IN ₂	14	17	EΝ₃
EN ₂	15	16	IN₃

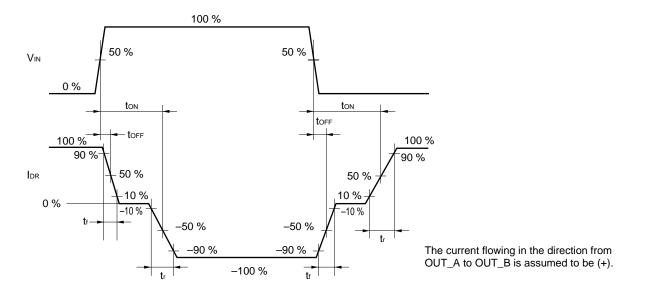
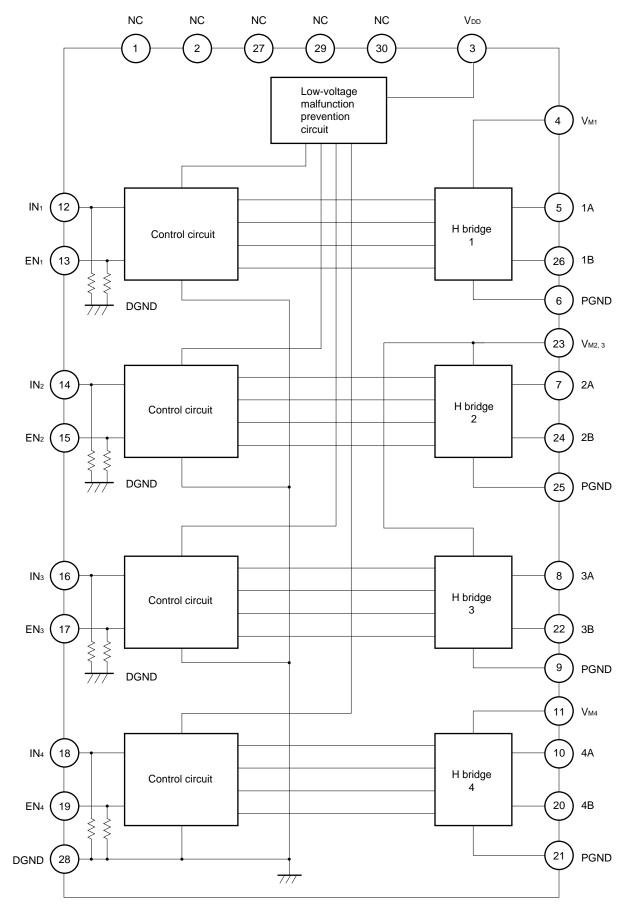


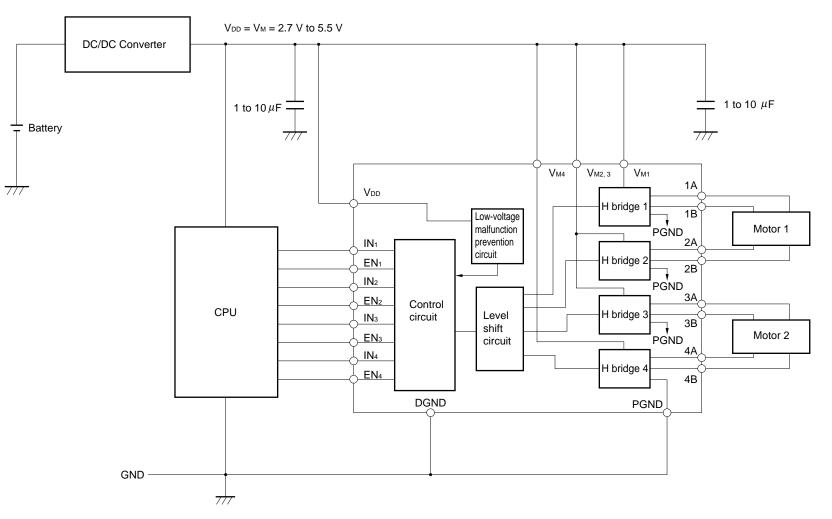
Figure 1. Switching Characteristic Wave

BLOCK DIAGRAM



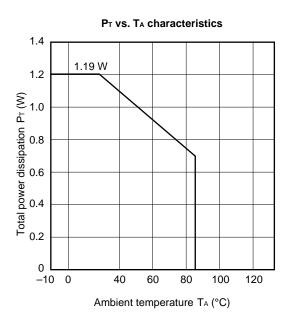




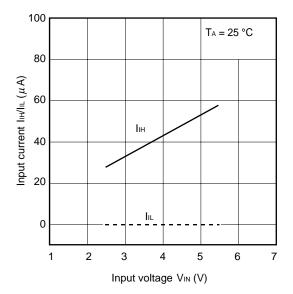


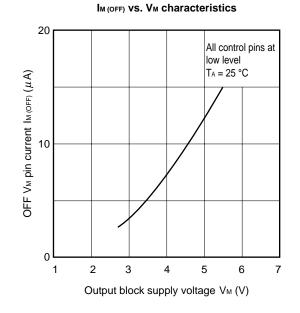
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TYPICAL CHARACTERISTICS (TA = 25 °C)

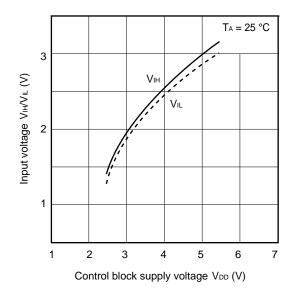








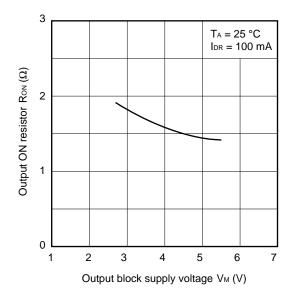
VIH/VIL vs. VDD characteristics

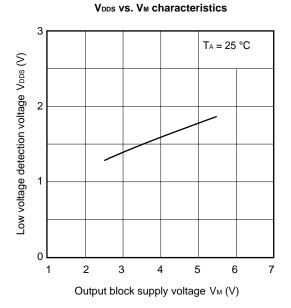


Data Sheet S13147EJ2V0DS

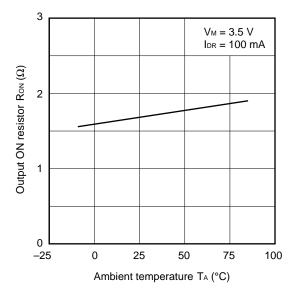
RIND vs. VDD characteristics

Ron vs. Vm characteristics

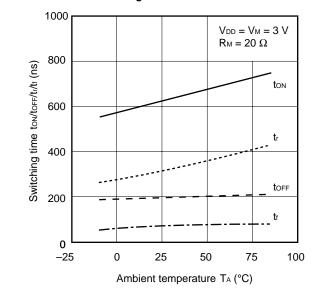




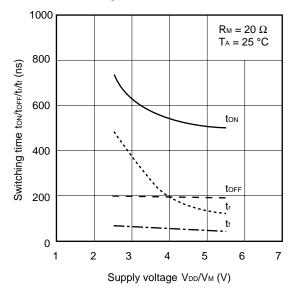




Switching time vs. TA characteristics

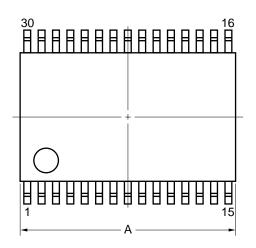


Switching time vs. VDD/VM characteristics

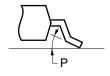


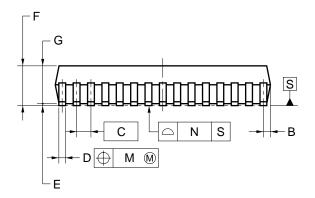
PACKAGE DIMENSION

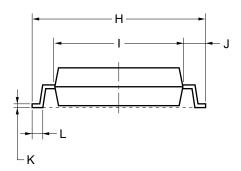
30-PIN PLASTIC SSOP (7.62 mm (300))



detail of lead end







NOTE

Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
A	9.85±0.26
В	0.51 MAX.
С	0.65 (T.P.)
D	$0.32^{+0.08}_{-0.07}$
E	0.125±0.075
F	2.0 MAX.
G	1.7±0.1
Н	8.1±0.2
I	6.1±0.2
J	1.0±0.2
К	$0.17\substack{+0.08\\-0.07}$
L	0.5±0.2
М	0.10
N	0.10
Р	$3^{\circ}^{+7^{\circ}}_{-3^{\circ}}$
	P30GS-65-300B-3

RECOMMENDED SOLDERING CONDITIONS

It is recommended to solder this product under the conditions described below.

For soldering methods and conditions other than those listed below, consult NEC.

For the details of the recommended soldering conditions of this type, refer to the **Semiconductor Device Mounting Technology Manual (C10535E)**.

Soldering Method	Soldering Conditions	Symbol of Recommended Soldering
Infrared reflow	Peak package temperature: 235 °C, Time: 30 seconds MAX. (210 °C MIN.), Number of times: 3 MAX., Number of days: None ^{Note} , Flux: Rosin-based flux with little chlorine content (chlorine: 0.2 Wt% MAX.) is recommended.	IR35-00-3
VPS	Peak package temperature: 215 °C, Time: 40 seconds MAX. (200 °C MIN.), (200 °C MIN.), Number of times: 2 MAX., Number of days: None ^{Note} , Flux: Rosin-based flux with little chlorine content (chlorine: 0.2 Wt% MAX.) is recommended.	VP15-00-2
Wave soldering	Soldering bath temperature: 260 °C MAX., Time: 10 seconds MAX., Preheating temperature: 120 °C MAX., Number of times: 1, Flux: Rosin-based flux with little chlorine content (chlorine: 0.2 Wt% MAX.) is recommended.	WS60-00-1

Note The number of storage days at 25 °C, 65% RH after the dry pack has been opened

Caution Do not use two or more soldering methods in combination.

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